

Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

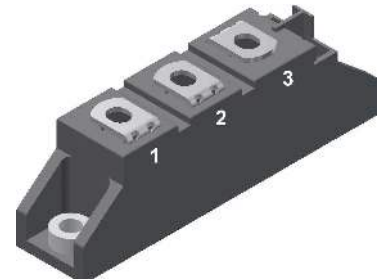
$$I_{FAV} = 110 \text{ A}$$

$$V_F = 1.14 \text{ V}$$

Phase leg

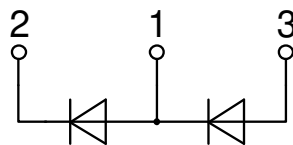
Part number

MDMA110P1200TG



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

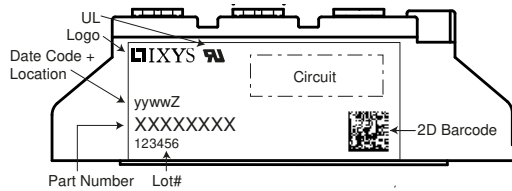
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		100	μA
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		2	mA
V_F	forward voltage drop	$I_F = 110$ A		$T_{VJ} = 25^\circ\text{C}$		1.21	V
		$I_F = 220$ A				1.44	V
		$I_F = 110$ A		$T_{VJ} = 125^\circ\text{C}$		1.14	V
		$I_F = 220$ A				1.44	V
I_{FAV}	average forward current	$T_C = 100^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		110	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.82	V
r_F	slope resistance					2.8	m Ω
R_{thJC}	thermal resistance junction to case					0.3	K/W
R_{thCH}	thermal resistance case to heatsink				0.2		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		415	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		2.00	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		2.16	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		1.70	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.84	kA
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		20.0	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		19.4	kA ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		14.5	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		14.0	kA ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		73	pF



Package TO-240AA		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				76		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second		4800		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V



Part description

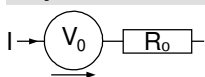
- M = Module
- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 110 = Current Rating [A]
- P = Phase leg
- 1200 = Reverse Voltage [V]
- TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA110P1200TG	MDMA110P1200TG	Box	36	514304

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Rectifier

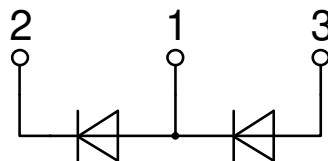
$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	1.6	mΩ



Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



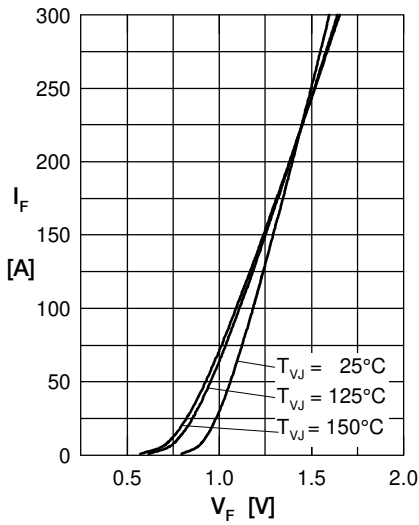
Rectifier


Fig. 1 Forward current versus voltage drop per diode

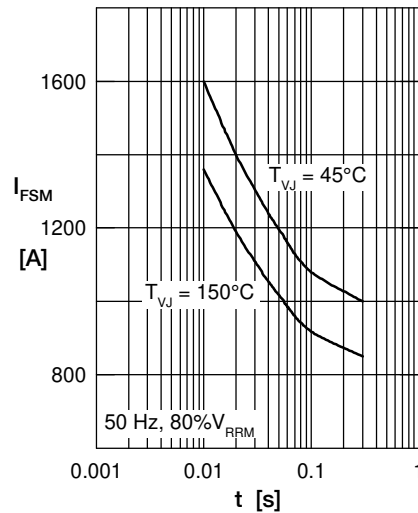


Fig. 2 Surge overload current vs. time per diode

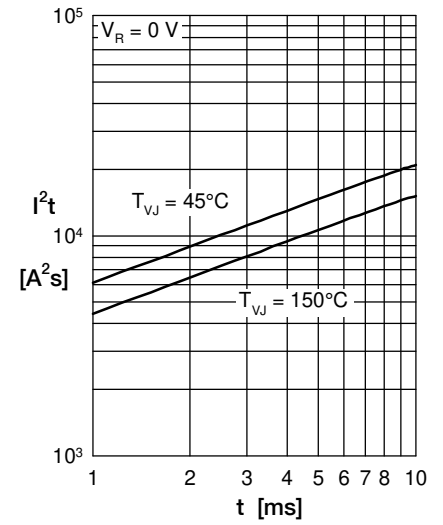
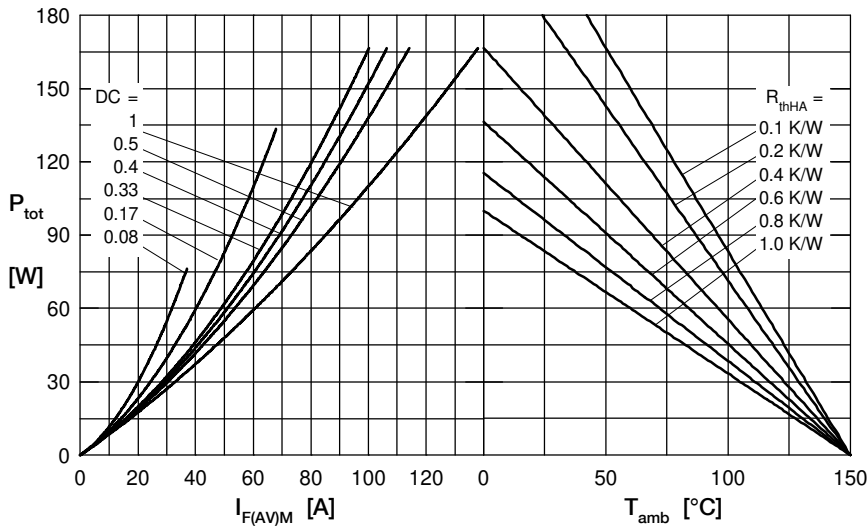

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

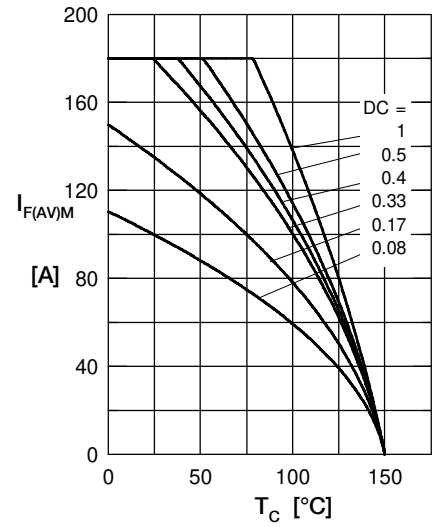


Fig. 5 Max. forward current vs. case temperature per diode

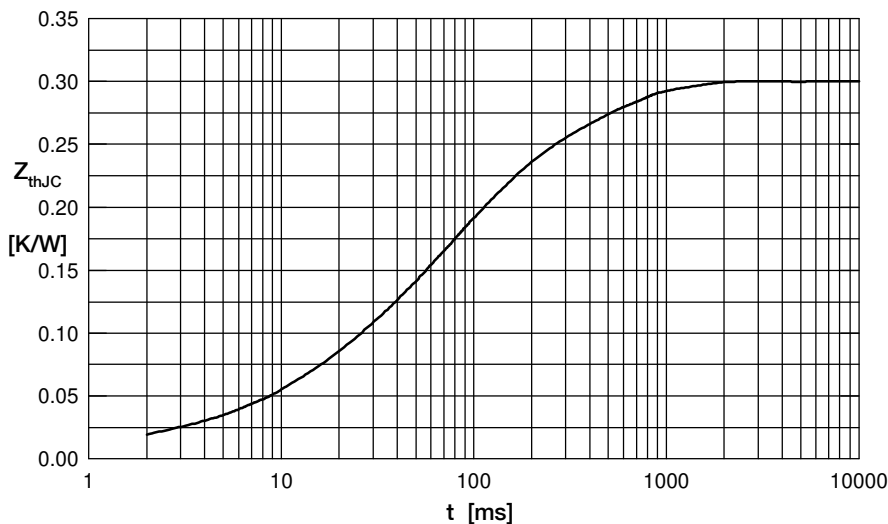


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.01	0.001
2	0.04	0.013
3	0.16	0.070
4	0.09	0.400